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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> EA 27 2008				Application Number	10/712,062
				Filing Date	November 14, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	1	of	1	Attorney Docket Number	0756-7218

[illegible][illegible]

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Office Action dated August 3, 1998 for Application Serial No. 08/784,293.	
		Office Action dated February 11, 1999 for Application No. 08/784,293.	
		Office Action dated January 17, 2003 for Application No. 08/784,293.	
Examiner Signature			Date Considered 

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U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
JP		4,330,363		Biegesen et al.	05/18/1982	
		4,996,077		Moslehi et al.	02/26/1991	
		5,089,441		Moslehi	02/18/1992	

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		EP	0 178 447			04/23/1986		Eng.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," Volume 60, No. 3, August 1, 1986, pp. 985-990, J. Applied Physics.	
		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 23, No. 12.	
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," Volume 1, 1986, pp. 207-211, Silicon Processing for the VLSI Era.	
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Volume 95, 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR.	
		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," June 1, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	
Examiner Signature	[Signature]		Date Considered
			2/10/06

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